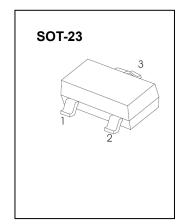
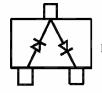


FEATURES

Low forward voltage : V_F (3) = 0.9V (typ.)
Fast reverse recovery time : t_{rr} = 1.6ns (typ.)

Small total capacitance : C_T = 0.9pF (typ.)





MARKING: C3

Maximum Ratings ,Single Diode @T_A=25℃

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	85	V
Peak Repetitive Peak reverse voltage	V_{RRM}		
Working Peak Reverse Voltage	V_{RWM}	80	V
DC Blocking Voltage	V_R		
Forward Continuous Current	I _{FM}	300	mA
Average Rectified Output Current	Io	100	mA
Peak forward surge current @=10ms	I _{FSM}	2	А
Power Dissipation	P _D	150	mW
Junction temperature	TJ	150	°C
Storage temperature	T _{STG}	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	I _R = 100uA	80		V
Reverse voltage leakage current	I _R	V _R =80V		0.5	uA
Forward voltage	V _F	I _F =100mA		1.2	V
Diode capacitance	C _D	V _R =0V , f=1MHz		3	pF
Reverse recovery time	t _{rr}	I _F =10mA		4	nS

www.htsemi.com



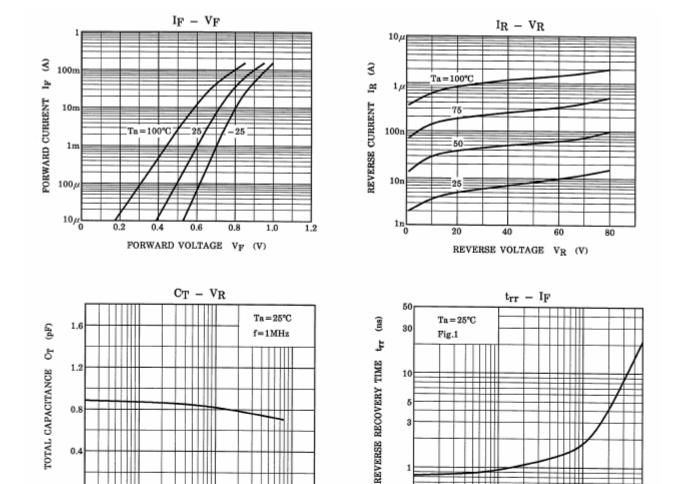
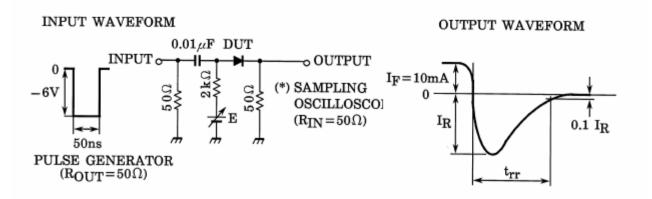


Fig.1 Reverse recovery time (t_{rr}) test circuit

REVERSE VOLTAGE V_R (V)

0.3



100

FORWARD CURRENT IF (mA)

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Diodes - General Purpose, Power, Switching category:

Click to view products by Jinyu manufacturer:

Other Similar products are found below:

MCL4151-TR3 MMBD3004S-13-F RD0306T-H RD0506LS-SB-1H RGP30G-E373 DSE010-TR-E BAQ333-TR BAQ335-TR BAQ33-GS18 BAS1602VH6327XT BAV17-TR BAV19-TR BAV301-TR BAW27-TAP HSC285TRF-E NSVBAV23CLT1G NTE525 1SS181-TP 1SS184-TP 1SS193,LF 1SS193-TP 1SS400CST2RA SBAV99LT3G SDAA13 LL4448-GS18 SHN2D02FUTW1T1G LS4150GS18 LS4151GS08 SMMBD7000LT3G FC903-TR-E 1N4449 1N4934-E3/73 1SS226-TP APT100DL60HJ RFUH20TB3S RGP30G-E354 RGP30M-E3/73 D291S45T MCL4151-TR BAS 16-02V H6327 BAS 21U E6327 BAS 28 E6327 BAS33-TAP BAS 70-02V H6327 BAV300-TR BAV303-TR3 BAW27-TR BAW56DWQ-7-F BAW56M3T5G BAW75-TAP